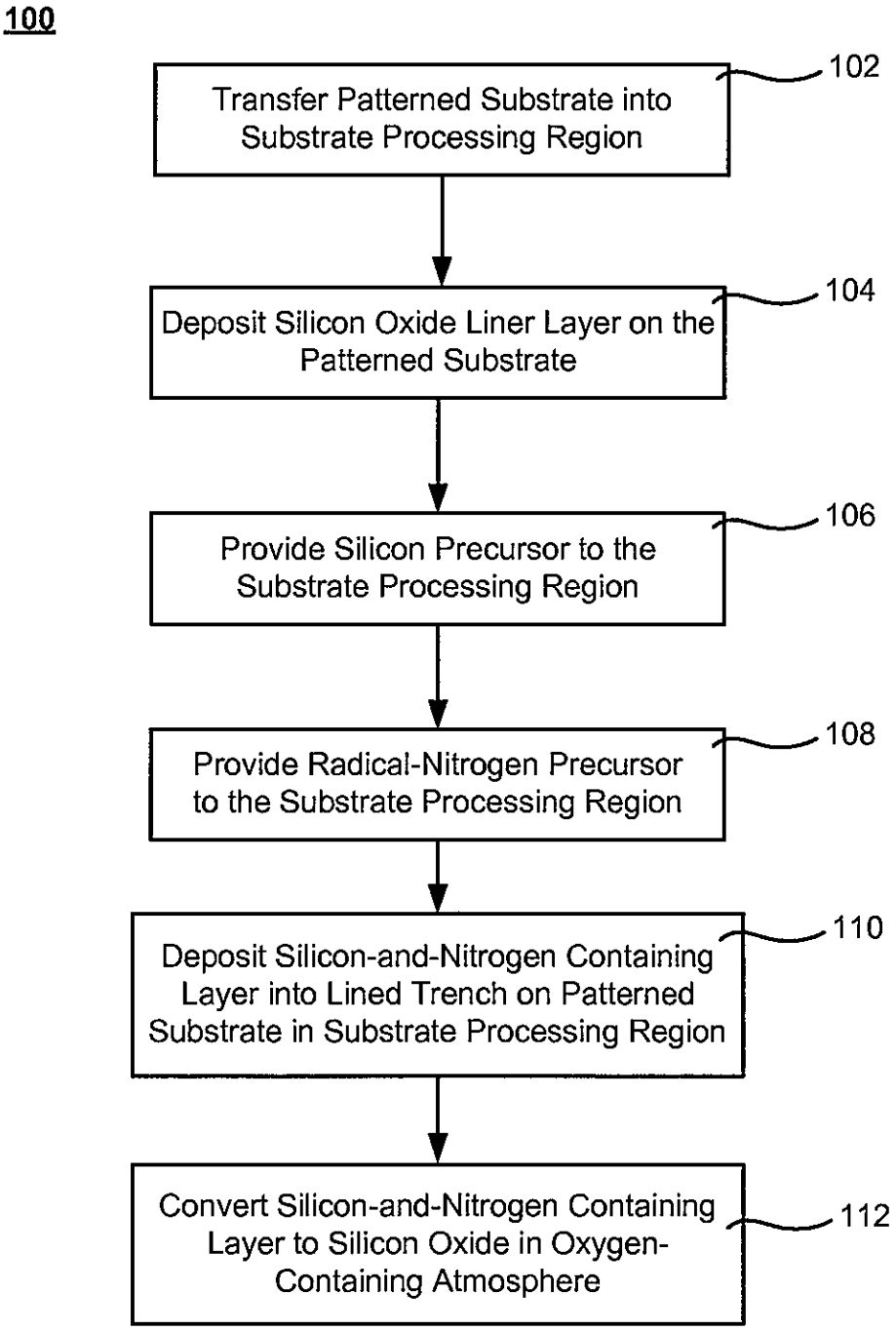

100
Transfer Patterned Substrate into Substrate Processing Region
102
Deposit Silicon Oxide Liner Layer on the Patterned Substrate
104
Provide Silicon Precursor to the Substrate Processing Region
106
Provide Radical-Nitrogen Precursor to the Substrate Processing Region
108
Deposit Silicon-and-Nitrogen Containing Layer into Lined Trench on Patterned Substrate in Substrate Processing Region
110
Convert Silicon-and-Nitrogen Containing Layer to Silicon Oxide in Oxygen-Containing Atmosphere
112

FIG 1

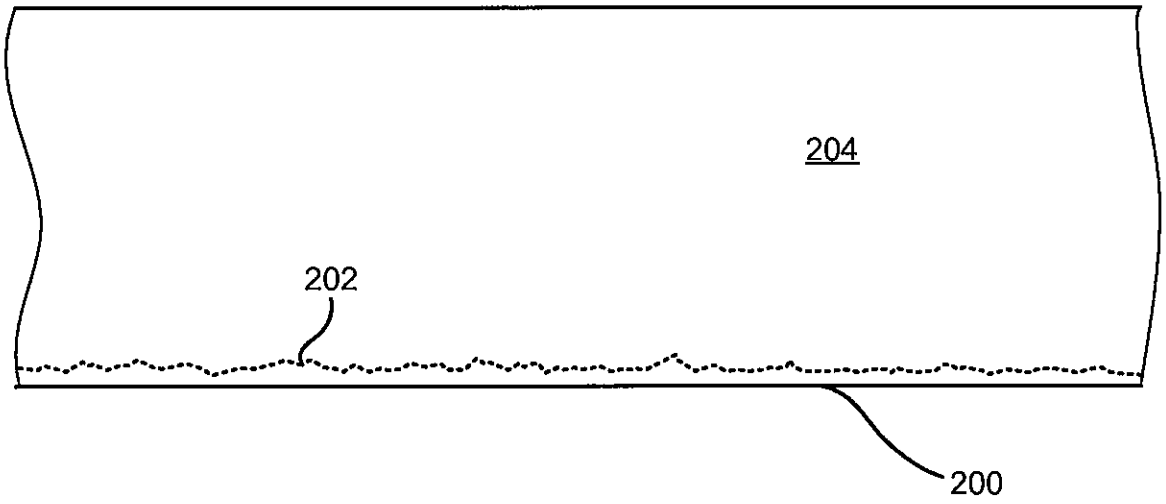


FIG 2

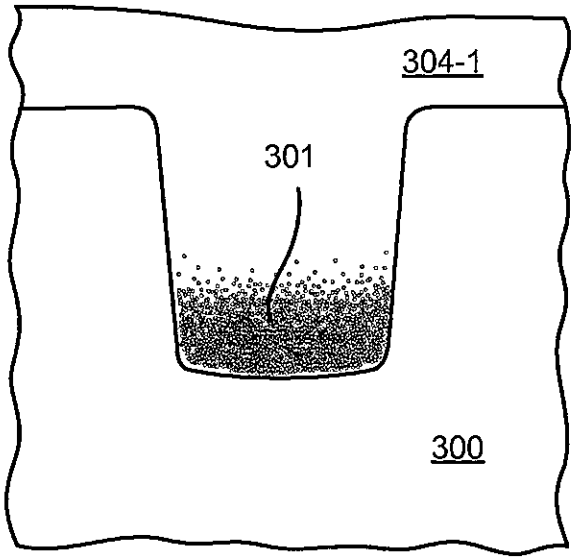


FIG 3A

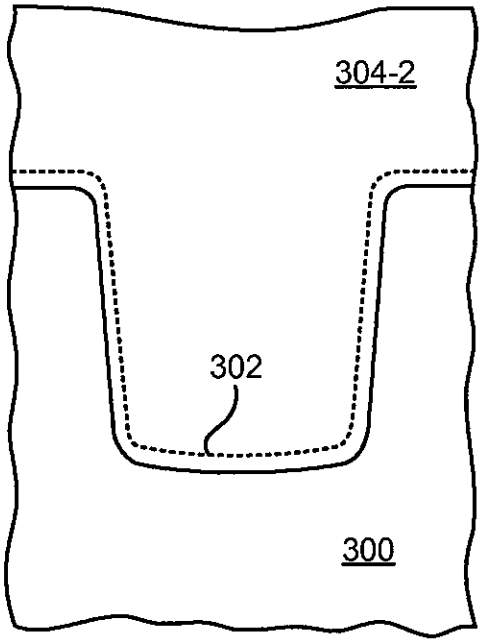


FIG 3B

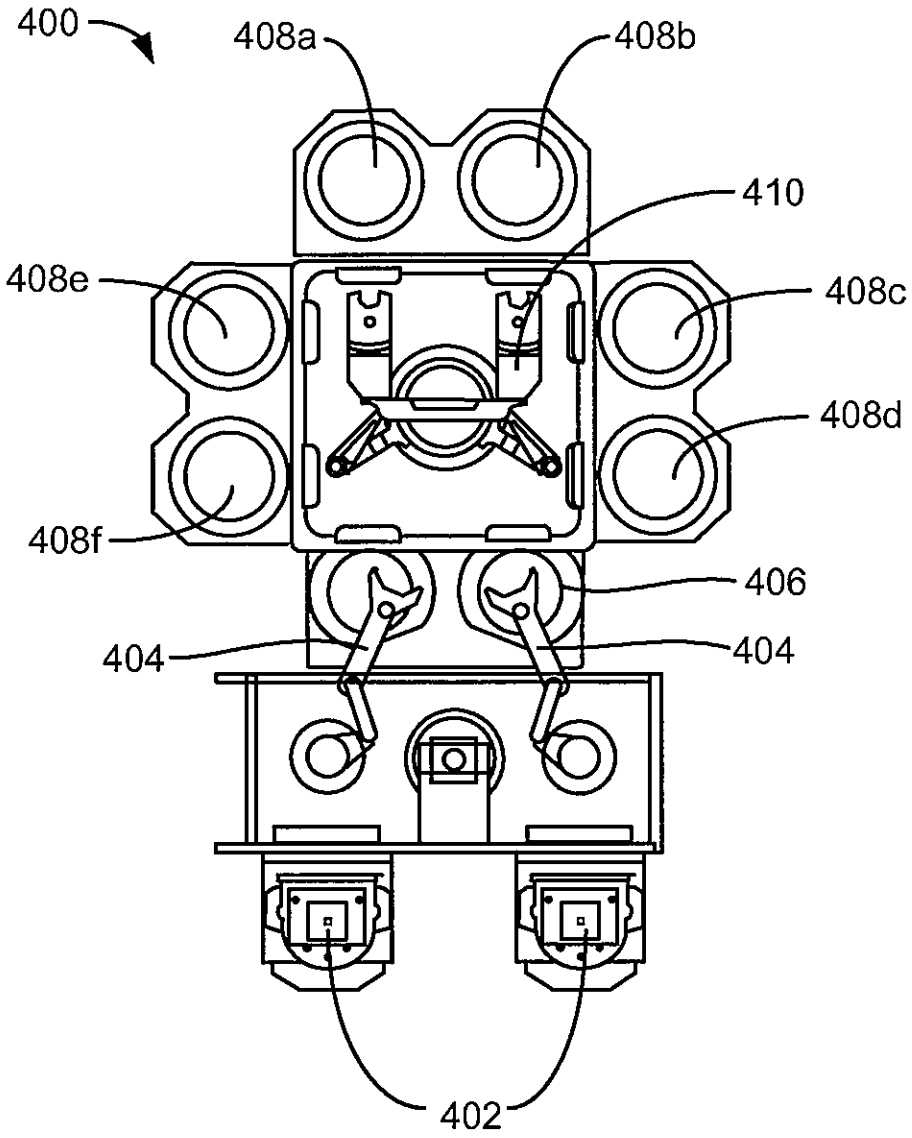


FIG. 4

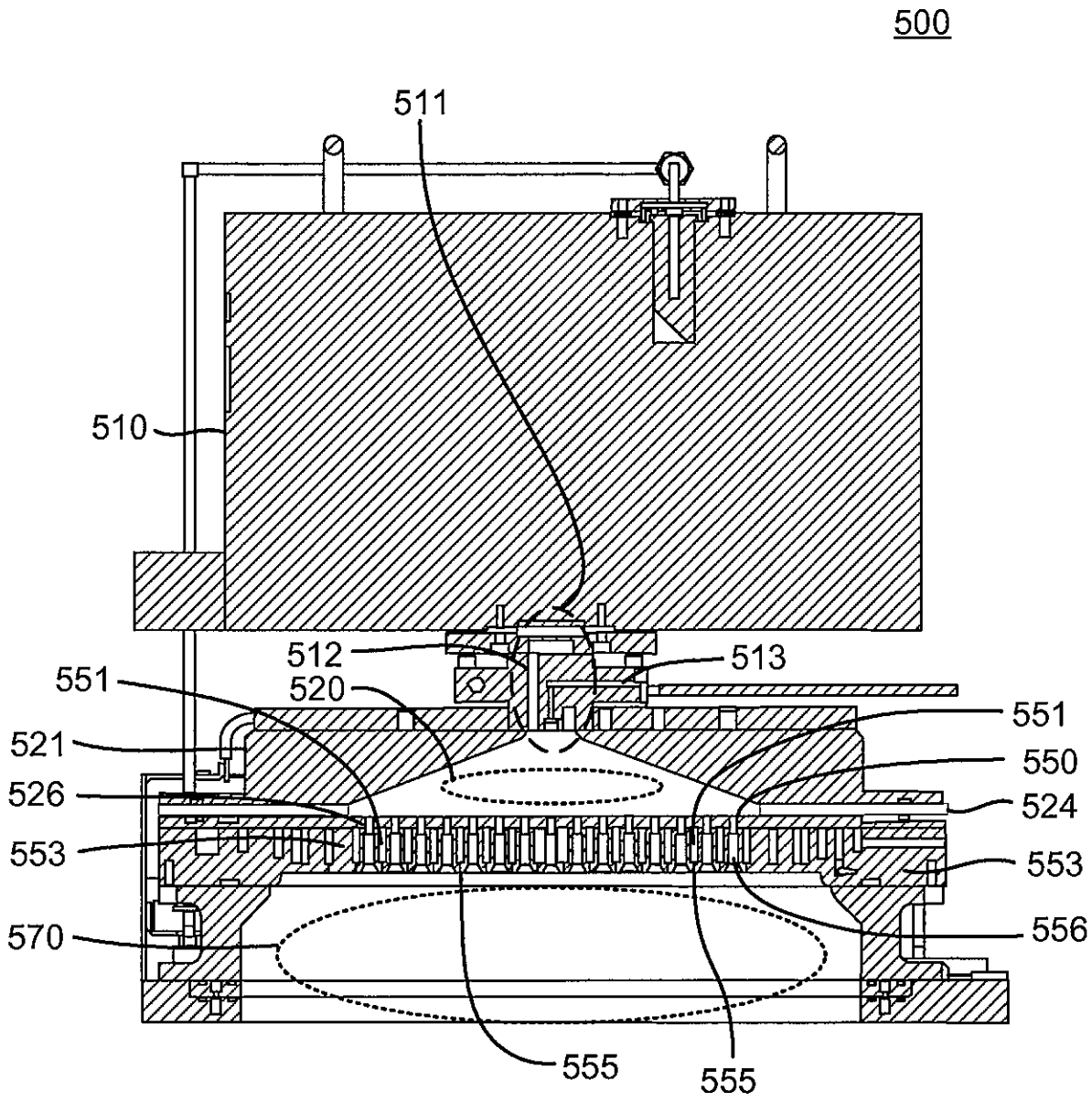

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FIG. 5A

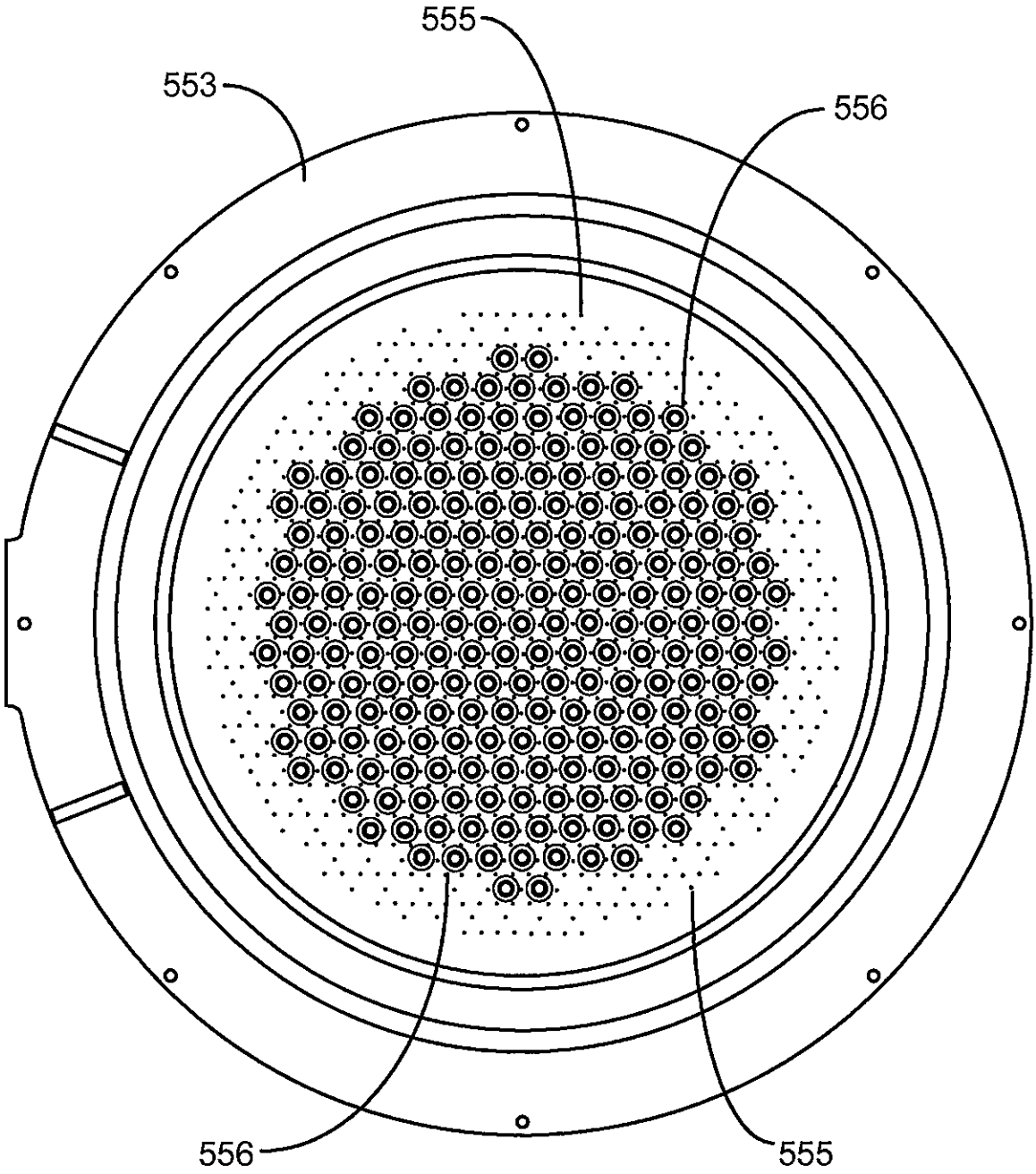


FIG. 5B